

Patent Assignment Abstract of Title

Total Assignments: 2
Application #: 09184490 **Filing Dt:** 11/02/1998

Patent #: 6325858 **Issue Dt:** 12/04/2001

PCT #: NONE

Publication #: NONE

Pub Dt:

JOHN F. WENGERT, IVO RAAIJMAKERS, MIKE HALPIN, LOREN JACOBS, MICHAEL J.

Inventors: MEYER, FRANK VAN BILSEN, MATT GOODMAN, ERIC BARRETT, ERIC WOOD, BLAKE SAMUELS

Title: LONG LIFE HIGH TEMPERATURE PROCESS CHAMBER

Assignment: 1
Reel/Frame: 010881/0362 **Received:** 07/14/2000 **Recorded:** 06/13/2000 **Mailed:** 08/22/2000 **Pages:** 15

Conveyance: CHANGE OF NAME (SEE DOCUMENT FOR DETAILS).

Assignor: ADVANCED SEMICONDUCTOR MATERIALS AMERICA, INC. **Exec Dt:** 12/12/1997

Assignee: ASM AMERICA, INC.

 3440 EAST UNIVERSITY DRIVE
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Correspondent: KNOBBE, MARTENS, OLSON & BEAR, LLP

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Assignment: 2
Reel/Frame: 009701/0741 **Received:** 01/21/1999 **Recorded:** 01/20/1999 **Mailed:** 04/17/1999 **Pages:** 8

Conveyance: ASSIGNMENT OF ASSIGNORS INTEREST (SEE DOCUMENT FOR DETAILS).

Assignors: WENGERT, JOHN F.
Exec Dt: 11/19/1998

RAAIJMAKER, IVO
Exec Dt: 10/23/1998

HALPIN, MIKE
Exec Dt: 11/16/1998

JACOBS, LOREN
Exec Dt: 10/29/1998

MEYER, MICHAEL J.
Exec Dt: 10/29/1998

VAN BILSEN, FRANK
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Search Results as of: 1/9/2003 1:57:36 P.M.

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Web interface last modified: Oct. 5, 2002

Patent Assignment Abstract of Title

Total Assignments: 1
Application #: 09439833 **Filing Dt:** 11/12/1999 **Patent #:** 6342691 **Issue Dt:** 01/29/2002

PCT #: NONE

Publication #: NONE **Pub Dt:**
Inventors: KRISTIAN E. JOHNSGARD, JEAN-FRANCOIS DAVIET, JAMES A. GIVENS, STEPHEN E. SAVAS, BRAD S. MATTSON, ASHUR J. ATANOS

Title: APPARATUS AND METHOD FOR THERMAL PROCESSING OF SEMICONDUCTOR SUBSTRATES

Assignment: 1

Reel/Frame: <u>010709/0817</u>	Received:	Recorded:	Mailed:	Pages:
	04/24/2000	04/14/2000	06/20/2000	2

Conveyance: ASSIGNMENT OF ASSIGNORS INTEREST (SEE DOCUMENT FOR DETAILS).

Assignors: <u>JOHNSGARD, KRISTIAN E.</u>	Exec Dt: 04/12/2000
<u>DAVIET, JEAN-FRANCOIS</u>	Exec Dt: 03/24/2000
<u>GIVENS, JAMES A.</u>	Exec Dt: 04/10/2000
<u>SAVAS, STEPHEN E.</u>	Exec Dt: 03/06/2000
<u>MATTSON, BRAD S.</u>	Exec Dt: 03/31/2000
<u>ATANOS, ASHUR J.</u>	Exec Dt: 04/12/2000

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Search Results as of: 1/9/2003 11:36:26 A.M.

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Patent Assignment Abstract of Title

Total Assignments: 1**Application #:** 09828550 **Filing Dt:** 04/06/2001**Patent #:** NONE**Issue Dt:****PCT #:** NONE**Publication #:** 20020011211**Pub Dt:** 01/31/2002**Inventor:** Michael W. Halpin**Title:** Barrier coating for vitreous materials**Assignment: 1****Reel/Frame:** 011687/0225 **Received:** 04/20/2001**Recorded:**
04/06/2001**Mailed:**
07/02/2001**Pages:** 2**Conveyance:** ASSIGNMENT OF ASSIGNORS INTEREST (SEE DOCUMENT FOR DETAILS).**Assignor:** HALPIN, MICHAEL W.**Exec Dt:** 04/06/2001**Assignee:** ASM AMERICA, INC.3440 EAST UNIVERSITY DRIVE
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Search Results as of: 1/9/2003 11:35:46 A.M.

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 Web interface last modified: Oct. 5, 2002

L Number	Hits	Search Text	DB	Time stamp
1	2	6342691.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 10:46
8	32	(("5902407") or ("5571333") or ("5514439") or ("5474618") or ("5421893") or ("5360269") or ("5336327") or ("5315092") or ("5246500") or ("5065698") or ("5027746") or ("4984904") or ("4978567") or ("4976996") or ("4592307") or ("4377347")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 10:54
15	1	(quartz or 'SiO ₂ ') and ("silicon nitride" or 'Si ₃ N ₄ ') and (((("5902407") or ("5571333") or ("5514439") or ("5474618") or ("5421893") or ("5360269") or ("5336327") or ("5315092") or ("5246500") or ("5065698") or ("5027746") or ("4984904") or ("4978567") or ("4976996") or ("4592307") or ("4377347")).PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 11:04
22	0	6120640.pn. and sputter\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 11:43
29	0	6120640.pn. and sputt\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 11:45
36	0	5910221.pn. and sputt\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 11:44
43	2	6120640.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 11:51
50	3349	(Sputter\$3 same thickness) same ("silicon nitride" or 'Si ₃ N ₄ ')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 12:14
57	1904	((Sputter\$3 same thickness) same ("silicon nitride" or 'Si ₃ N ₄ ')) and protect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 11:59
64	475	((Sputter\$3 same thickness) same ("silicon nitride" or 'Si ₃ N ₄ ')) and protect\$3) and (thickness same ("mu.m" or angstrom))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 12:15
71	33	(((Sputter\$3 same thickness) same ("silicon nitride" or 'Si ₃ N ₄ ')) and protect\$3) and (thickness same ("mu.m" or angstrom))) and corrosiv\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 12:00
78	442	(((Sputter\$3 same thickness) same ("silicon nitride" or 'Si ₃ N ₄ ')) and protect\$3) and (thickness same ("mu.m" or angstrom))) not (((((Sputter\$3 same thickness) same ("silicon nitride" or 'Si ₃ N ₄ ')) and protect\$3) and (thickness same ("mu.m" or angstrom))) and corrosiv\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 12:04
85	181	((((Sputter\$3 same thickness) same ("silicon nitride" or 'Si ₃ N ₄ ')) and protect\$3) and (thickness same ("mu.m" or angstrom))) not (((((Sputter\$3 same thickness) same ("silicon nitride" or 'Si ₃ N ₄ ')) and protect\$3) and (thickness same ("mu.m" or angstrom))) and corrosiv\$5)) and (chamber or reactor or vessel or tank)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 12:15

92	35	((Sputter\$3 same thickness) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same ("mu.m" or angstrom)) and lifetime	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:13
99	291	(Sputter\$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:18
106	53	((Sputter\$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same ("mu.m" or angstrom))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:15
113	20	((Sputter\$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same ("mu.m" or angstrom)) and (chamber or reactor or vessel or tank)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:17
120	271	((Sputter\$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) not (((Sputter\$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same ("mu.m" or angstrom)) and (chamber or reactor or vessel or tank))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:17
127	9	((Sputter\$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) not (((Sputter\$3 same wall) same ("silicon nitride" or 'si.sub.3 n.sub.4')) and (thickness same ("mu.m" or angstrom)) and (chamber or reactor or vessel or tank)) and lifetime	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:17
134	464	(Sputter\$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with (protect\$4 or prevent\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:21
141	5	((Sputter\$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with (protect\$4 or prevent\$4)) and (118/\$.ccls. or 156/\$.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:26
148	1	(Sputter\$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with lifetime	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:26
155	43	(Sputter\$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with wall	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:27
162	2	((Sputter\$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) with wall) and (118/\$.ccls. or 156/\$.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:26
169	51	(Sputter\$3 with ("silicon nitride" or 'si.sub.3 n.sub.4')) and 118/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 12:28

L Number	Hits	Search Text	DB	Time stamp
1	2	6342691.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 10:46
8	32	(("5902407") or ("5571333") or ("5514439") or ("5474618") or ("5421893") or ("5360269") or ("5336327") or ("5315092") or ("5246500") or ("5065698") or ("5027746") or ("4984904") or ("4978567") or ("4976996") or ("4592307") or ("4377347")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 10:54
15	1	(quartz or 'SiO ₂ .sub.2') and ("silicon nitride" or 'Si.sub.3 N.sub.4') and ((("5902407") or ("5571333") or ("5514439") or ("5474618") or ("5421893") or ("5360269") or ("5336327") or ("5315092") or ("5246500") or ("5065698") or ("5027746") or ("4984904") or ("4978567") or ("4976996") or ("4592307") or ("4377347")).PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/09 11:04